

L Number	Hits	Search Text	DB	Time stamp
-	83	laser same anneal\$3 same (silicon or si) and 117/904.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/05 15:58
-	12	laser same anneal\$3 same (silicon or si) and 117/\$4.ccls. and (CVD or chemical adj vapor adj deposition) same plasma and ion near3 beam	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/05 16:58
-	78	laser same anneal\$3 same (silicon or si) and 117/\$4.ccls. and (CVD or chemical adj vapor adj deposition) same plasma same (si or silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/05 16:05
-	41	laser same anneal\$3 same (silicon or si) and 117/\$4.ccls. and (CVD or chemical adj vapor adj deposition) same plasma same (si or silicon) and apparatus	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/05 16:25
-	15	laser same (kev) same anneal\$3 and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/05 16:58
-	5	(CVD or chemical adj vapor adj deposition) same plasma and 117/98.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/05 17:01
-	19	(CVD or chemical adj vapor adj deposition) same (si or silicon) and 117/98.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/05 17:03
-	51	(CVD or chemical adj vapor adj deposition) same plasma same ion same beam and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/05 17:04
-	118	((CVD or chemical adj vapor adj deposition) same plasma) and 117/\$4.ccls. and ion near3 beam	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/05 17:09
-	63	((CVD or chemical adj vapor adj deposition) same plasma) same (silicon or si) and 117/\$4.ccls. and ion near3 beam	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/06 09:42
-	43	(CVD or chemical adj vapor adj deposition) same (silicon or si) and 117/\$4.ccls. and ion near3 beam same (ar or argon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/06 10:19

L Number	Hits Search Text	DB	Time stamp
-	76 beam same (si or silicon) same (layer or film) same ion same amorphous and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/09 16:49
-	12 CVD near3 ion same (si or silicon) and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/09 16:53
-	109 CVD same plasma same ion and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/09 17:02
-	68 ion same (si or silicon) same (amorphous or seed or nucleus) same (beam or implant\$4) and 117/84-109.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/10 13:25
-	5 ion same (si or silicon) same (amorphous or seed or nucleus) same (assist\$3) and 117/84-109.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/10 13:27
-	17 ion same (si or silicon) same ECR and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/10 13:38
-	51 (si or silicon) same (ECR or "electron cyclotron resonance") and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/10 13:40
-	19 (si or silicon) same (ECR or "electron cyclotron resonance") same ion and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/10 14:58
-	82 ion same substrate same (beam) same amorphous and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/10 15:16
-	14 ion same substrate same (beam) same (si or silicon) same (nucle\$4) and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/10 15:50
-	41 ion same substrate same (si or silicon) same (nucle\$4) and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/10 16:08
-	127 ion same substrate same (si or silicon) same (clean\$3 or sputter\$3) and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/10 16:54
-	17 ion same substrate same (si or silicon) same (clean\$3 or sputter\$3) same ev and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/10 17:07

9	ion same (si or silicon) same amorphous same ev and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/10 17:10
6	CVD same plasma same ev same (si or silicon) and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/10 17:16
31	CVD same plasma same (si or silicon) same energy and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/10 17:12
4	CVD same plasma same kev same (si or silicon) and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/10 17:16
73	ion same (si or silicon) same amorphous same energy and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/11 09:45
83	ion same (si or silicon) same amorphous same beam and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/11 10:08
81	ion same (si or silicon) same polycrystal\$4 same beam and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/11 10:26
24	ion same (si or silicon) same assist\$4 and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/11 10:44
11	plasma same cvd same ion same (kev or ev) and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/11 11:11
38	ion near2 beam same (kev or ev) same (si or silicon) and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/12 11:31
21	ion near2 beam same (kev or ev) same sputter\$3 and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/12 13:23
32	ion near2 beam same mov\$4 and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/12 13:37
27	ion same mov\$4 near4 substrate and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/12 14:06
59	ion near3 beam same nucle\$5 and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/12 16:37

-	17	ion near3 beam same seed\$3 and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/12 16:45
-	17	ion near3 beam same clean\$3 and mbe and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/12 17:06
-	21	ion near3 beam same (oxide or native) and mbe and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/12 17:10
-	138	ion same nucle\$4 and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/13 09:22
-	43	ion same substrate same (si or silicon) same beam same \$3treat\$4 and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/13 09:50